

7-Unit 400mA Darlington Transistor Array

IR2C20/IR2C20N

T-52-13-45

IR2C20/IR2C20N 7-Unit 400mA Darlington Transistor Array

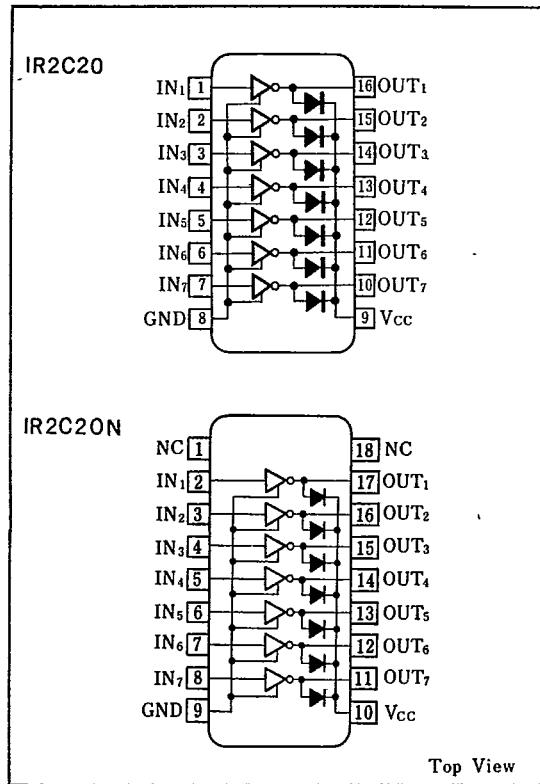
■ Description

The IR2C20/IR2C20N is a 7-circuit driver. The internal clamping diodes enable the IC to drive the inductive load directly.

■ Features

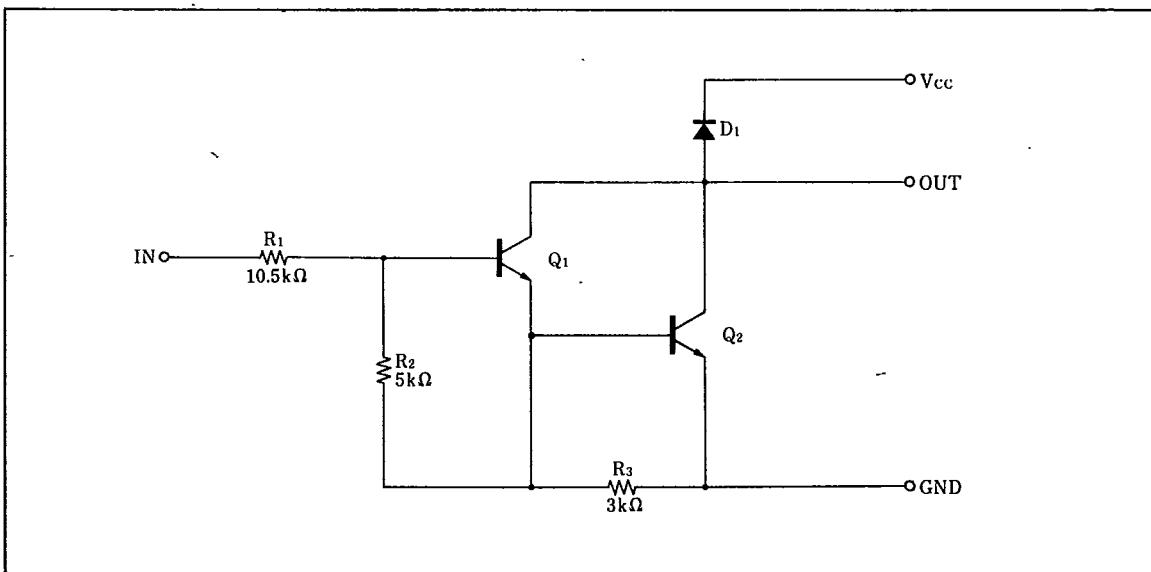
1. High output current $I_{OUT}=400\text{mA}$ (MAX.)
2. High output breakdown voltage
 $BV_{CEO}=50\text{V}$ (MAX.)
3. Directly driven by MOS output
4. Internal output clamping diode
5. Darlington construction
6. 16-pin dual-in-line package (IR2C20)
18-pin mini-flat package (IR2C20N)

■ Pin Connections



Top View

■ Equivalent Circuit



SHARP

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Absolute Maximum Ratings

Parameter	Symbol	Condition		Rating	Unit
Supply voltage	V _{CC}			45	V
Output current*1	I _{OUT}	Each circuit		400	mA
Input voltage	V _{IN}			0~V _{CC}	V
Collector-emitter breakdown voltage	BV _{CEO}			50	V
Forward current	I _F	For clamp diode		40	mA
Surge current	I _{surge}	For clamp diode		400	mA
Load inductance	L _L			100	mH
Power dissipation	P _D	T _a ≤25°C	IR2C20	1,000	mW
			IR2C20N	450	
P _D derating ratio	ΔP _D /°C	T _a >25°C	IR2C20	10	mW/°C
			IR2C20N	3.6	
Operating temperature	T _{opr}			-25~+75	°C
Storage temperature	T _{stg}			-55~+150	°C

*1 Duty cycle: 15% or less, repetitive frequency: 10Hz or more

**Recommended Operating Conditions**

Parameter	Symbol	Condition		Rating	Unit
Output voltage	V _{CEO}			50	V
Output current	I _{OUT}	at 15% duty		0~400	mA
		at 50% duty		0~200	

Electrical Characteristics

(Ta = -25~+75°C)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{CC}				50	V
ON-State input current	I _{I ON}	V _{IN} =10V, I _{OUT} =0mA		0.9	1.5	mA
ON-State voltage	V _{O ON1}	V _{IN} =8V, I _{OUT} =400mA			2.2	
	V _{O ON2}	V _{IN} =8V, I _{OUT} =200mA			1.4	V
OFF-State output current	I _{I OFF}	V _{IN} =0V, V _{CEO} =50V			100	μA
Diode forward voltage	V _F	For clamp diode, I _{surge} =400mA			2.2	V
Diode leakage current	I _R	For clamp diode, V _R =50V			100	μA
DC current amplitude	h _{FE}	V _{CEO} =2.5V, I _{OUT} =300mA, Ta=25°C	1,000			
Input "High" voltage	V _{IN ON}	I _{OUT} =400mA	8.0			V
Input "Low" voltage	V _{IN LOW}				1.0	V
Input capacity	C _{IN}	f=1MHz		9		pF

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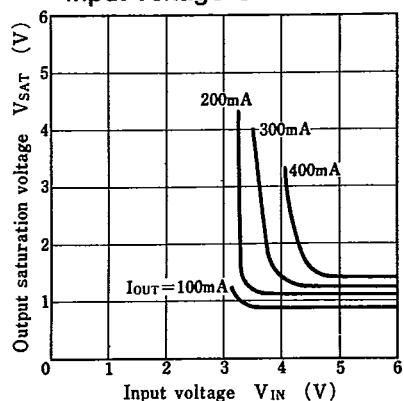
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■ Electrical Characteristic Curves (Unless otherwise specified, $T_a=25^\circ\text{C}$)

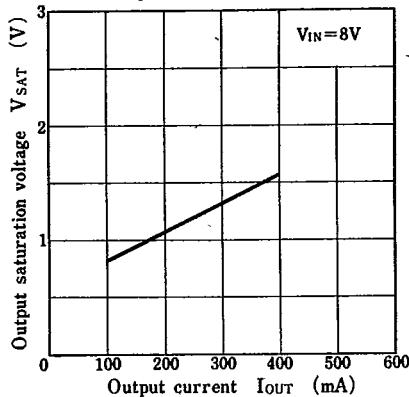
Output saturation voltage—

Input voltage Characteristics

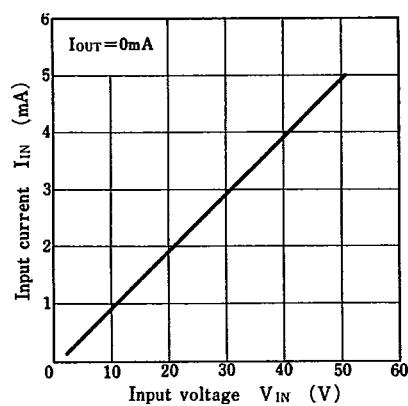


Output saturation voltage—

Output current Characteristics

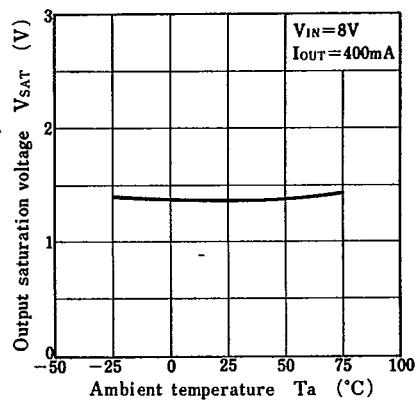


Input current—Input voltage Characteristics

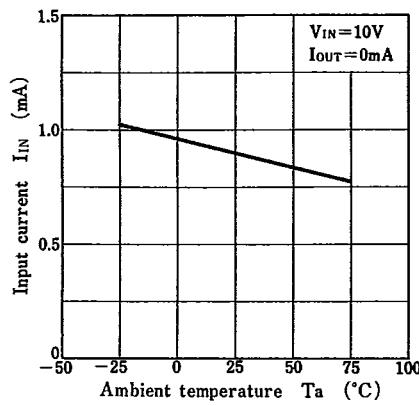


Output saturation voltage—

Ambient temperature Characteristics



Input current—Ambient temperature Characteristics



Output current—Duty cycle Characteristics

